LAPT

2SC2922

Silicon NPN Epitaxial Planar Transistor (Complement to type 2SA1216)

Application : Audio and General Purpose

Absolute maximum ratings (Ta=25°C)

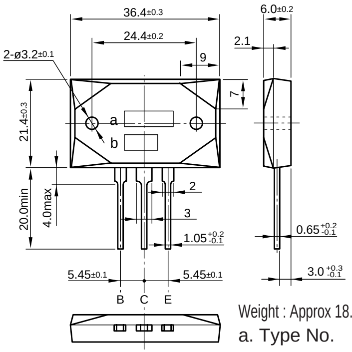
Symbol	2SC2922	Unit
V_{CBO}	180	V
V_{CEO}	180	V
V_{EBO}	5	V
I_C	17	A
I_B	5	A
P_C	200(Tc=25°C)	W
Tj	150	°C
Tstg	–55 to +150	°C

Electrical Characteristics (Ta=25°C)

Symbol	Conditions	2SC2922	Unit
I_{CBO}	V_{CB}=180V	100max	µA
I_{EBO}	V_{EB}=5V	100max	µA
$V_{(BR)CEO}$	I_C=25mA	180min	V
h_{FE}	V_{CE}=4V, I_C=8V	30min*	
$V_{CE(sat)}$	I_C=8A, I_B=0.8A	2.0max	V
f_T	V_{CE}=12V, I_E=–2A	50typ	MHz
C_{OB}	V_{CB}=10V, f=1MHz	250typ	pF

*h_{FE} Rank $\overline{O}$(30 to 60), Y(50 to 100), P(70 to 140), G(90 to 180)

External Dimensions MT-200

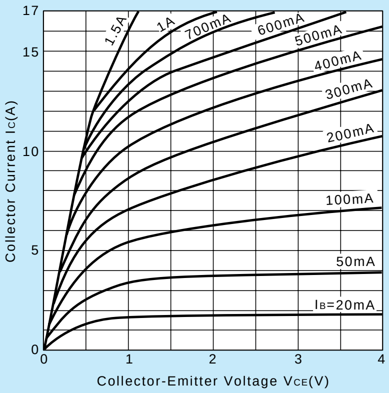


Weight : Approx 18.4g
a. Type No.
b. Lot No.

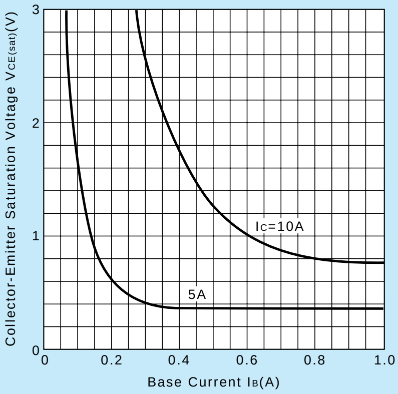
Typical Switching Characteristics (Common Emitter)

V_{CC} (V)	R_L (Ω)	I_C (A)	V_{B2} (V)	I_{B1} (A)	I_{B2} (A)	ton (µs)	tstg (µs)	tf (µs)
40	4	10	–5	1	–1	0.2typ	1.3typ	0.45typ

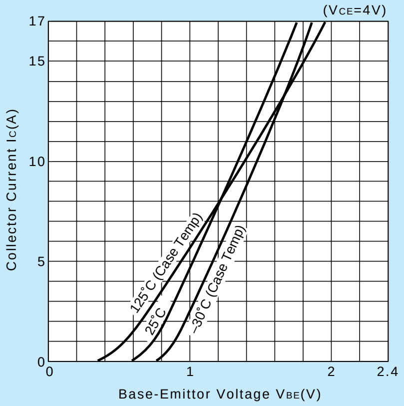
I_C–V_{CE} Characteristics (Typical)



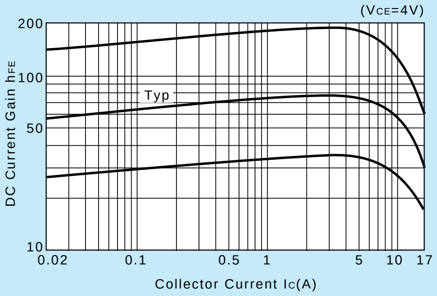
$V_{CE(sat)}$–I_B Characteristics (Typical)



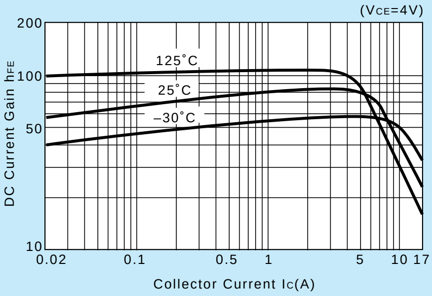
I_C–V_{BE} Temperature Characteristics (Typical)



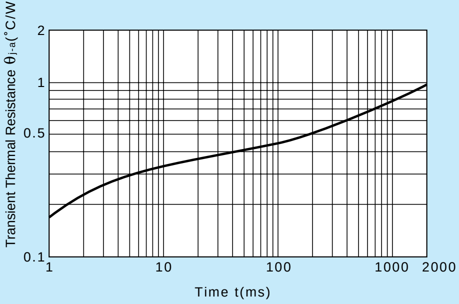
h_{FE}–I_C Characteristics (Typical)



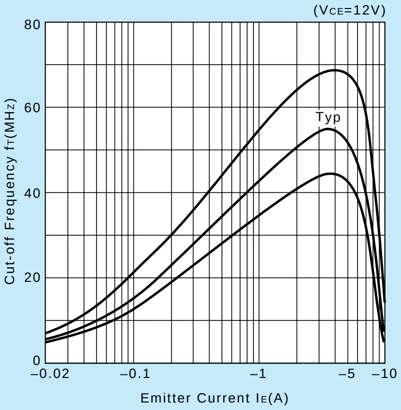
h_{FE}–I_C Temperature Characteristics (Typical)



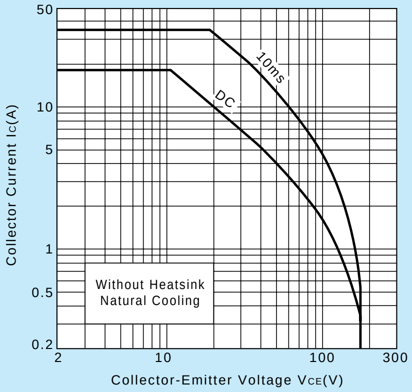
θ_{j-a}–t Characteristics



f_T–I_E Characteristics (Typical)



Safe Operating Area (Single Pulse)



P_C–Ta Derating